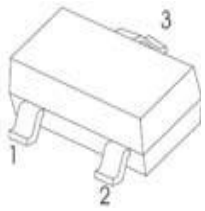
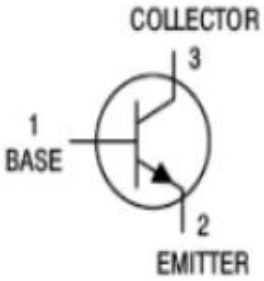
TRANSI STOR (PNP)	SOT-23 Plastic-Encapsulate Transistors

SOT-23





1.BASE
2.EMITTER
3.COLLECTOR

Marking :2TY

Features

※ Complimentary to S8050

※ Collector Current: Ic=0.5A

MAXIMUM RATINGS (Ta=25℃ unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	VCBO	−40	V
Collector-Emitter Voltage	VCEO	−25	V
Emitter-Base Voltage	VEBO	−5	V
Collector Current	IC	−500	mA
Collector Power Dissipation	PC	300	mW
Thermal Resistance From Junction To Ambient	RΘJA	417	℃/W
Junction Temperature	Tj	150	℃
Storage Temperature	Tstg	−55～+150	℃

ELECTRICAL CHARACTERISTICS (Ta=25℃ unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Collector-base breakdown voltage	V(BR)CBO	IC= -100μA, IE=0	-40	-86	-200	V
Collector-emitter breakdown voltage	V(BR)CEO	IC= -1mA, IB=0	-25	-50	-100	V
Emitter-base breakdown voltage	V(BR)EBO	IE= -100μA, IC=0	-5	-11	-30	V
Collector cut-off current	ICBO	VCB= -40 V , IE=0			-0.1	μA
Collector cut-off current	ICEO	VCB= -25V , IE=0			-1.4	μA
Emitter cut-off current	IEBO	VEB= -6V , IC=0			-0.1	μA
DC current gain	hFE	VCE=1V, IC= 50mA	100		400	
	hFE	VCE=1V, IC= 500mA	50			
Collector-emitter saturation voltage	VCE(sat)	IC= 500 mA, IB= 50mA			-0.6	V
Base-emitter saturation voltage	VBE(sat)	IC= 500 mA, IB= 50mA			-1.2	V
Transition frequency	fT	VCE=6V, IC= 20mA f=30MHz	150			MHz

CLASSIFICATION OF hFE

Rank	**H**
Range	**200-350**
MARKING:	**2TY**

TYPICAL ELEC TRICAL AND THERMAL CHARACTERISTICS

